Ordering number:EN3974

NPN Epitaxial Planar Silicon Transistor

2SC4735

27MHz CB Transceiver Driver Applications

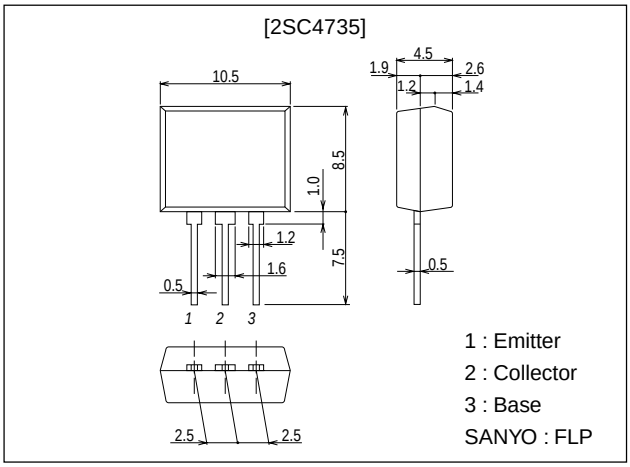
Features

- Large power type such as P_C=1.5W when used without heatsink.
- It is possible to make appliances more compact because its height on board is 9.5mm.
- Effective in automatic inserting and counting stocked amount because of being provided for radial taping.

Package Dimensions

unit:mm

2084B



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		75	V
Collector-to-Emitter Voltage	V_{CER}	R_{BE}=150Ω	75	V
	V_{CEO}		45	V
Emitter-to-Base Voltage	V_{EBO}		5	V
Collector Current	I_C		1.0	A
Collector Current (Pulse)	I_{CP}		1.5	A
Base Current	I_B		200	mA
Collector Dissipation	P_C		1.5	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=40V, I_E=0			1.0	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0			1.0	μA
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=500mA	60*		320*	
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=50mA	180	250		MHz
Output Capacitance	C_{ob}	V_{CB}=10V, f=1MHz		10	20	pF

* : The 2SC4735 are classified by 500mA h_{FE} as follows :

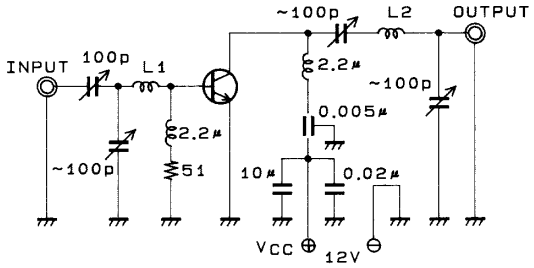
60	D	120	100	E	200	160	F	320

SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

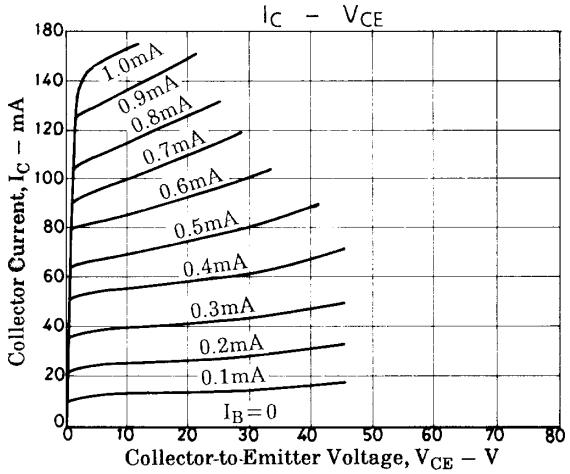
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Output Power	P_O	V_{CC}=12V, f=27MHz, Pi=35mW	1.0	1.8		W
Collector Efficiency	ηc	See specified test circuit.	60			%
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA, I_B=50mA		0.2	0.6	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=500mA, I_B=50mA		0.9	1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=10μA, I_E=0	75			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CER}$	I_C=1mA, R_{BE}=150Ω	75			V
	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	45			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	5			V

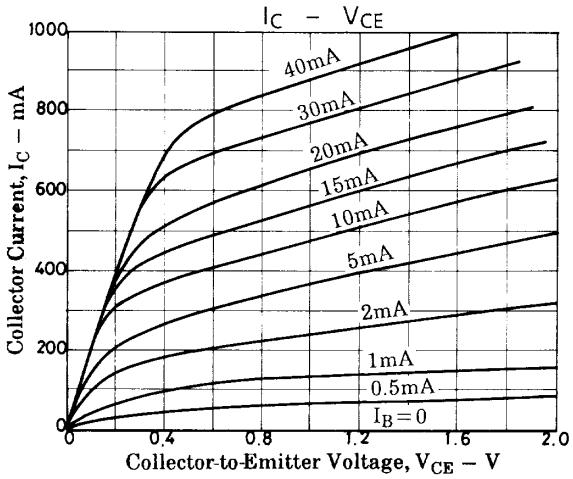
Collector Effieiency Test Circuit

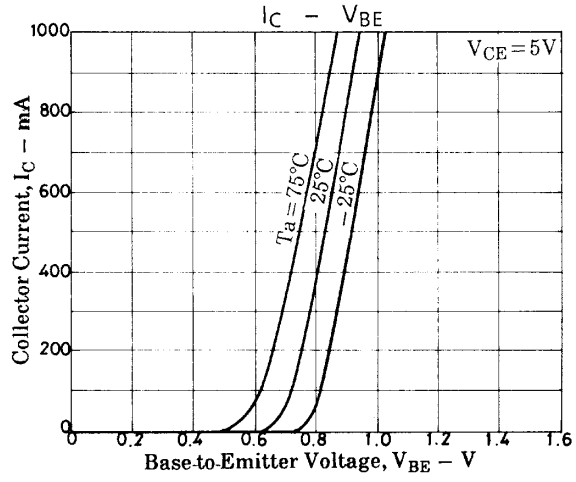


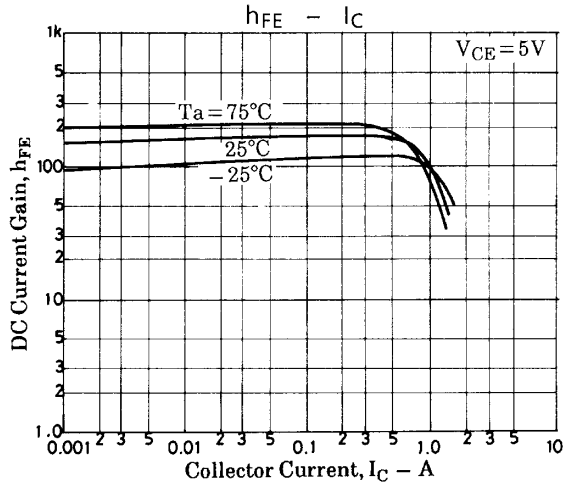
L1 : 10φ 0.6φ EC 6T
L2 : 10φ 0.6φ EC 12T

Unit (resistance : Ω, capacitance : F)

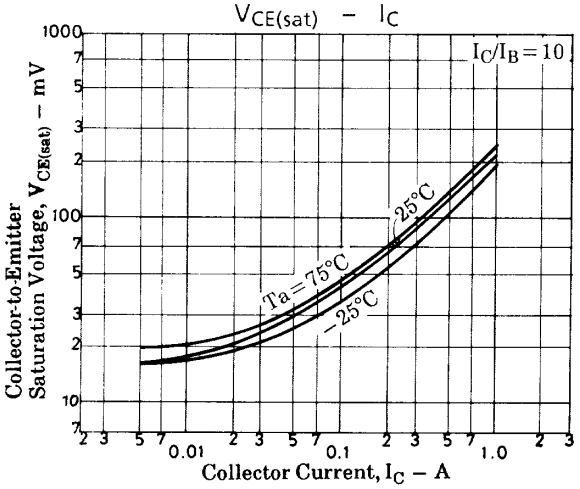




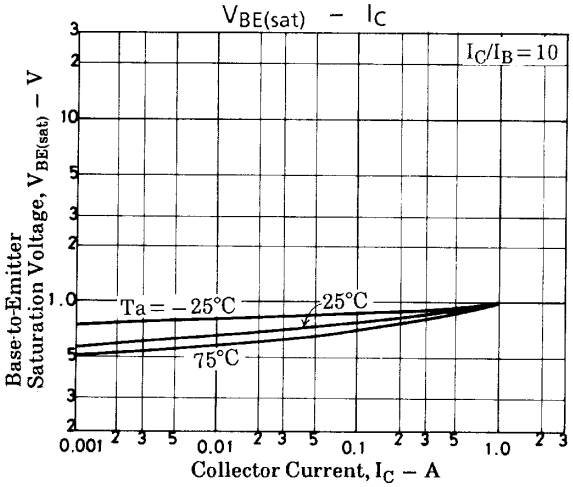




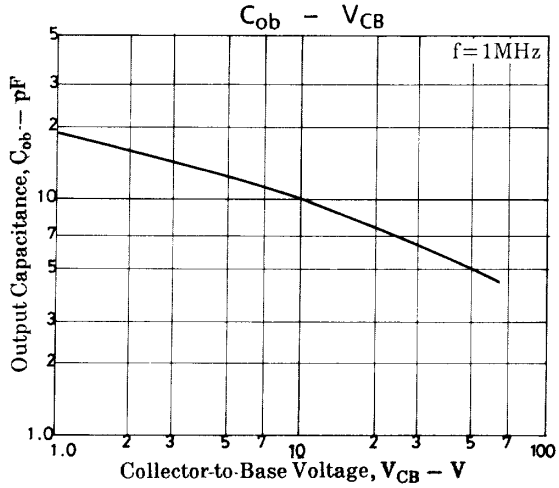
$V_{CE(sat)}$ – I_C



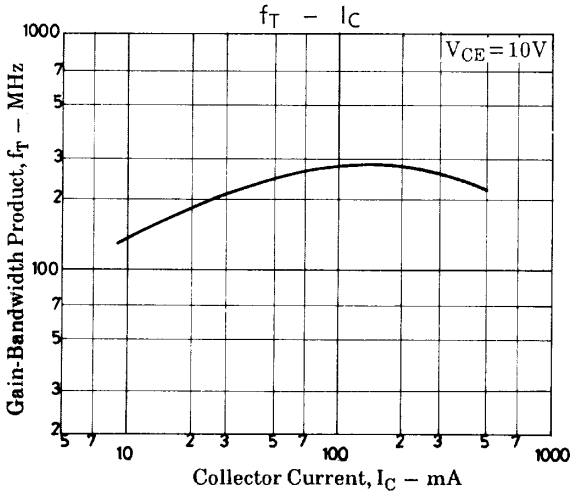
$V_{BE(sat)}$ – I_C



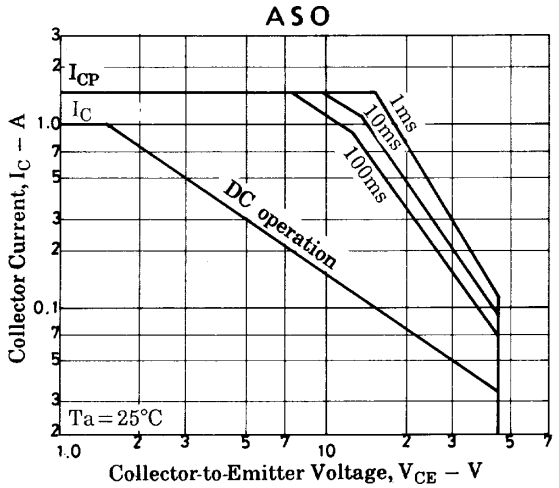
C_{ob} – V_{CB}



f_T – I_C



ASO



P_C – Ta